

TENTATIVE TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TC7W66F, TC7W66FU

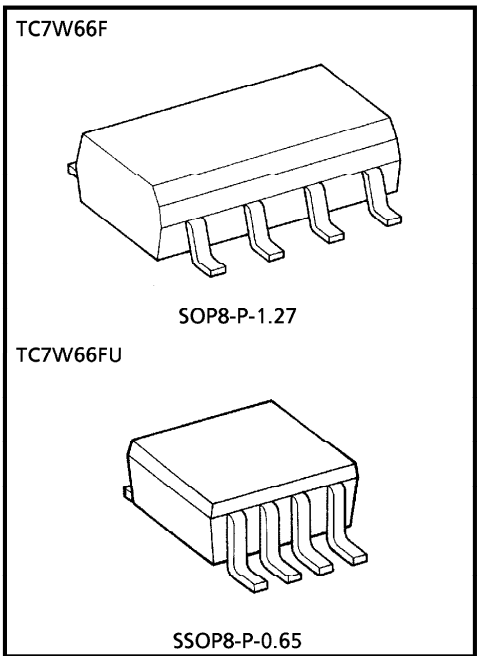
(UNDER DEVELOPMENT)

DUAL BILATERAL SWITCH

The TC7W66 is a high speed CMOS DUAL BILATERAL SWITCH fabricated with silicon gate CMOS technology. It consists of four independent high speed switches capable of controlling either digital or analog signals while maintaining the CMOS low power dissipation. Control input (C) is provided to control the switch. The switch turns ON while the C input is high, and the switch turns OFF while low. All inputs are equipped with protection circuits against static discharge or transient excess voltage.

FEATURES

- High Speed $t_{pd} = 7ns$ (Typ.) at $V_{CC} = 5V$
- Low Power Dissipation $I_{CC} = 1\mu A$ (Max.) at $T_a = 25^\circ C$
- High Noise Immunity $V_{NIH} = V_{NIL} = 28\% V_{CC}$ (Min.)
- Low ON Resistance $R_{ON} = 50\Omega$ (Typ.) at $V_{CC} = 9V$
- High Degree of Linearity $THD = 0.05$ (Typ.) at $V_{CC} = 5V$
- Pin and Function Compatible with TC4W66

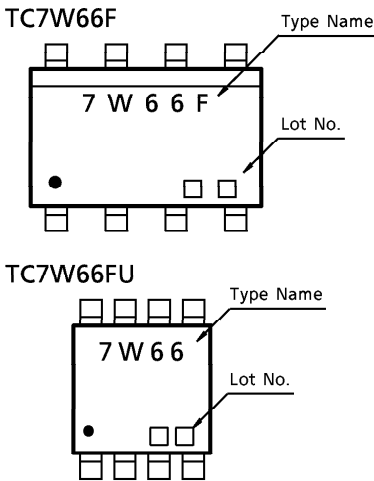


Weight SOP8-P-1.27 : 0.05g (Typ.)
SSOP8-P-0.65 : 0.02g (Typ.)

MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage Range	V_{CC}	$-0.5 \sim 13$	V
Control Input Voltage	V_{IN}	$-0.5 \sim V_{CC} + 0.5$	V
Switch I/O Voltage	$V_{I/O}$	$-0.5 \sim V_{CC} + 0.5$	V
Control Input Diode Current	I_{CK}	± 20	mA
I/O Diode Current	$I_{I/O}$	± 20	mA
Switch Through Current	I_T	± 25	mA
DC V_{CC}/GND Current	I_{CC}	± 50	mA
Power Dissipation	P_D	300	mW
Storage Temperature	T_{stg}	$-65 \sim 150$	$^\circ C$
Lead Temperature (10 s)	T_L	260	$^\circ C$

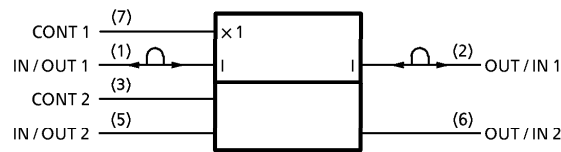
MARKING



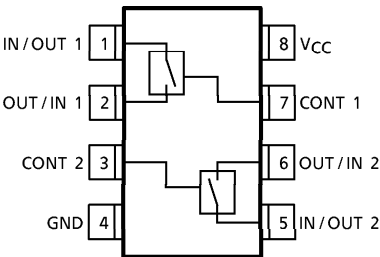
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LOGIC SYMBOL



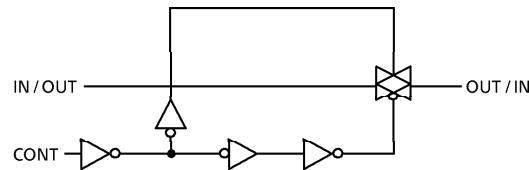
PIN ASSIGNMENT (TOP VIEW)



TRUTH TABLE

CONTROL	SWITCH FUNCTION
H	ON
L	OFF

LOGIC DIAGRAM (1 / 2 TC7W66)



RECOMMENDED OPERATING CONDITIONS

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage	V_{CC}	2~12	V
Control Input Voltage	V_{IN}	0~ V_{CC}	V
Switch I/O Voltage	$V_{I/O}$	0~ V_{CC}	V
Operating Temperature	T_{opr}	-40~85	°C
Input Rise and Fall Time	t_r, t_f	0~1000 ($V_{CC} = 2.0V$)	ns
		0~500 ($V_{CC} = 4.5V$)	
		0~400 ($V_{CC} = 6.0V$)	
		0~250 ($V_{CC} = 10.0V$)	

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DC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	TEST CONDITION	Ta = 25°C				Ta = - 40~85°C		UNIT
			V _{CC}	MIN.	TYP.	MAX.	MIN.	MAX.	
High-Level Control Input Voltage	V _{IHC}		2.0	1.5	—	—	1.5	—	V
			4.5	3.15	—	—	3.15	—	
			9.0	6.3	—	—	6.3	—	
			12.0	8.4	—	—	8.4	—	
Low-Level Control Input Voltage	V _{ILC}		2.0	—	—	0.5	—	0.5	V
			4.5	—	—	1.35	—	1.35	
			9.0	—	—	2.7	—	2.7	
			12.0	—	—	3.6	—	3.6	
ON Resistance	R _{ON}	V _{IN} = V _{IHC} V _{I/O} = V _{CC} to GND I _{I/O} ≤ 1mA	4.5	—	96	170	—	200	Ω
			9.0	—	55	85	—	100	
			12.0	—	45	80	—	90	
		V _{IN} = V _{IHC} V _{I/O} = V _{CC} or GND I _{I/O} ≤ 1mA	2.0	—	160	—	—	—	
			4.5	—	70	100	—	130	
			9.0	—	50	75	—	95	
			12.0	—	45	70	—	90	
			Difference of ON Resistance Between Switches	ΔR _{ON}	V _{IN} = V _{IHC} V _{I/O} = V _{CC} to GND I _{I/O} ≤ 1mA	4.5	—	10	
9.0	—	5				—	—	—	
12.0	—	5				—	—	—	
Input / Output Leakage Current (SWITCH OFF)	I _{OFF}	V _{OS} = V _{CC} or GND V _{IS} = GND or V _{CC} V _{IN} = V _{ILC}	12.0	—	—	± 100	—	± 1000	nA
Switch Input Leakage Current (SWITCH ON OUTPUT OPEN)	I _{Iz}	V _{OS} = V _{CC} or GND V _{INH} = V _{IHC}	12.0	—	—	± 100	—	± 1000	nA
Control Input Current	I _{IN}	V _{IN} = V _{CC} or GND	6.0	—	—	± 100	—	± 1000	nA
Quiescent Supply Current	I _{CC}	V _{IN} = V _{CC} or GND	6.0	—	—	1.0	—	10.0	μA
			9.0	—	—	4.0	—	40.0	
			12.0	—	—	8.0	—	80.0	

AC ELECTRICAL CHARACTERISTICS ($C_L = 50\text{pF}$, Input $t_r = t_f = 6\text{ns}$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	Ta = 25°C			Ta = -40~85°C		UNIT
			V _{CC}	MIN.	TYP.	MAX.	MIN.	MAX.
Phase Difference Between Input and Output	$\phi_{I/O}$		2.0	—	10	50	—	65
			4.5	—	4	10	—	13
			9.0	—	3	8	—	10
			12.0	—	3	7	—	9
Output Enable Time	t_{pZL} t_{pZH}	$R_L = 1\text{k}\Omega$	2.0	—	18	100	—	125
			4.5	—	8	20	—	25
			9.0	—	6	12	—	22
			12.0	—	6	12	—	18
Output Disable Time	t_{pLZ} t_{pHZ}	$R_L = 1\text{k}\Omega$	2.0	—	20	115	—	145
			4.5	—	10	23	—	29
			9.0	—	8	20	—	25
			12.0	—	8	18	—	22
Maximum Control Input Frequency		$R_L = 1\text{k}\Omega$ $C_L = 15\text{pF}$ $V_{OUT} = 1/2V_{CC}$	2.0	—	30	—	—	—
			4.5	—	30	—	—	—
			9.0	—	30	—	—	—
			12.0	—	30	—	—	—
Control Input Capacitance	C_{IN}		—	5	10	—	10	pF
Switch Terminal Capacitance	$C_{I/O}$		—	6	—	—	—	pF
Feed Through Capacitance	C_{IOS}		—	0.5	—	—	—	pF
Power Dissipation Capacitance	C_{pD}	(Note 1)	—	15	—	—	—	pF

(Note 1) : C_{pD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation :

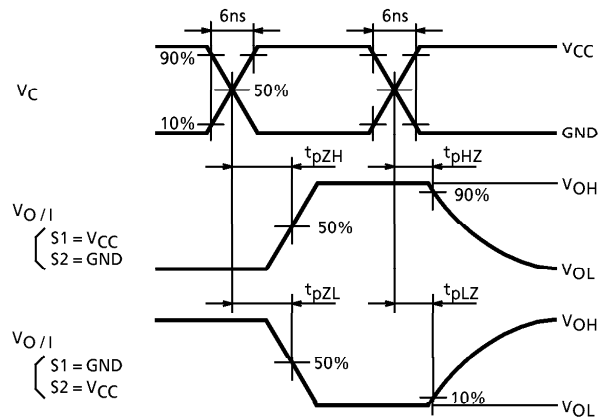
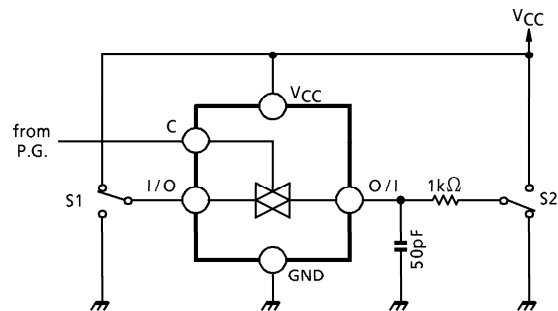
$$I_{CC(opr)} = C_{pD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/2$$

ANALOG SWITCH CHARACTERISTICS (GND = 0V, Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	V _{CC}	TYP.	UNIT
Sine Wave Distortion (T.H.D)		f _{IN} = 1kHz, V _{IN} = 4.0Vp-p @V _{CC} = 4.5V R _L = 10kΩ, V _{IN} = 8.0Vp-p @V _{CC} = 9.0V C _L = 50pF	4.5	0.05	%
			9.0	0.04	
Frequency Response (Switch ON)	f _{MAX}	Adjust f _{IN} voltage to obtain 0dBm at V _{OS} Increase f _{IN} Frequency until dB Meter reads -3dB R _L = 50Ω, C _L = 10pF f _{IN} = 1MHz, Sine Wave	4.5	200	MHz
			9.0	200	
Feedthrough Attenuation (Switch OFF)		V _{in} is centered at V _{CC} / 2 Adjust input for 0dBm R _L = 600Ω, C _L = 50pF f _{IN} = 1MHz, Sine Wave	4.5	- 60	dB
			9.0	- 60	
Crosstalk (Control Input to Signal Output)		R _L = 600Ω, C _L = 50pF f _{IN} = 1MHz, Square Wave (t _r = t _f = 6ns)	4.5	60	mV
			9.0	100	
Crosstalk (Between any switches)		Adjust V _{IN} to obtain 0dBm at Input R _L = 600Ω, C _L = 50pF f _{IN} = 1MHz, Sine Wave	4.5	- 60	dB
			9.0	- 60	

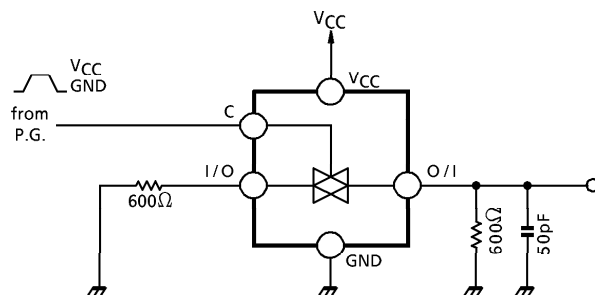
SWITCHING CHARACTERISTICS TEST CIRCUITS

1. t_{pLZ} , t_{pHZ} , t_{pZL} , t_{pZH}

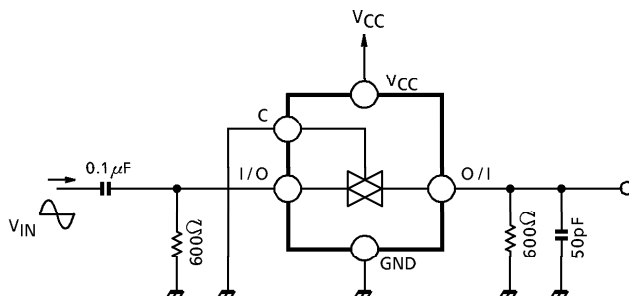


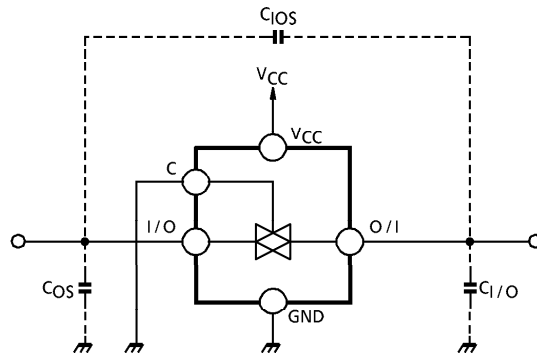
2. CROSS TALK (CONTROL INPUT-SWITCH OUTPUT)

$f_{in} = 1\text{MHz}$, duty = 50%, $t_r = t_f = 6\text{ns}$

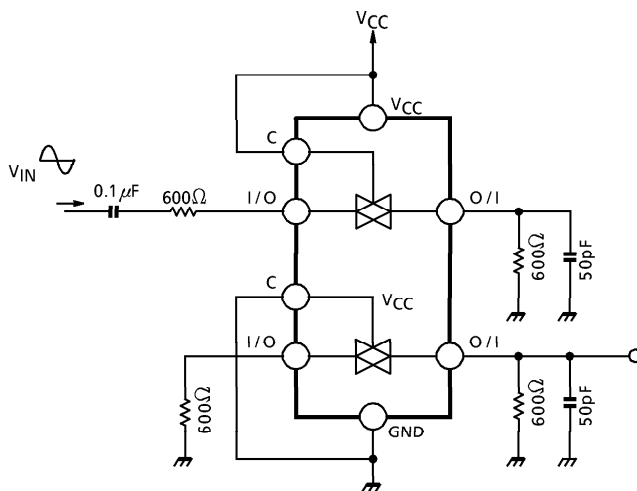


3. FEEDTHROUGH ATTENUATION



4. Clos, $C_{I/O}$ 

5. CROSS TALK (BETWEEN ANY TWO SWITCHES)



6. FREQUENCY RESPONSE (SWITCH ON)

